

# FDN340P

# Single P-Channel, Logic Level, PowerTrench $^{\rm O}$ MOSFET

### **General Description**

This P-Channel Logic Level MOSFET is produced using Fairchild Semiconductor advanced Power Trench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

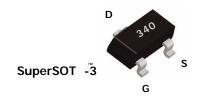
These devices are well suited for portable electronics applications: Load switching and power management, battery charging circuits, and DC/DC conversion.

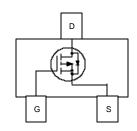
### **Features**

-2 A, 20 V.  $R_{DS(ON)} = 0.07$  Ω @ V  $_{GS} = -4.5$  V  $R_{DS(ON)} = 0.11$  Ω @ V  $_{GS} = -2.5$  V.

 $R_{DS(ON)} = 0.210 \Omega @ V_{GS} = -1.8 V.$ 

- Low gate charge (8nC typical).
- High performance trench technology for extremely low  $R_{DS(\text{ION})}$ .
- High power version of industry Standard SOT-23 package. Identical pin-out to SOT-23 with 30% higher power handling capability.





# Absolute Maximum Ratings T<sub>A=25°C</sub> unless otherwise noted

Symbol	Parameter	Ratings	Units	
$V_{\text{DSS}}$	Drain-Source Voltage	-20	V	
$V_{GSS}$	Gate-Source Voltage	±8	V	
l <sub>D</sub>	Drain Current - Continuous	(Note 1a)	-2	Α
	- Pulsed		-10	
P <sub>D</sub>	Power Dissipation for Single Operation (Note 1a)		0.5	W
		(Note 1b)	0.46	v
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperat	-55 to +150	°C	

### **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	250	°C/W
Rejc	Thermal Resistance, Junction-to-Case	(Note 1)	75	°C/W

## Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
340	FDN340P	7"	8mm	3000 units

Electric	al Characteristics	T <sub>A</sub> = 25°C unless otherwise noted	i			Ī
Symbol	Parameter	Min	Тур	Max	Units	
Off Char	acteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-20			V
<u>ΔBV DSS</u> ΔTJ	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}, \text{Referenced to } 25^{\circ}\text{C}$		-15		mV/°C
l <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V},  V_{GS} = 0 \text{ V}$ $T_{J} = 55^{\circ}\text{C}$			-1 -10	μΑ
Igssf	Gate-Body Leakage, Forward	$V_{GS} = 8 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I <sub>GSSR</sub>	Gate–Body Leakage, Reverse	$V_{GS} = -8 \text{ V}$ $V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)	1		ı		I
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{CS}, I_D = -250 \mu A$	-0.4	-0.9	-1.5	V
ΔV <sub>GS(th)</sub> ΔT <sub>J</sub>	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$ , Referenced to 25°C		2.7		mV/°C
R <sub>DS(on)</sub>	Static Drain-Source	$V_{GS} = -4.5 \text{ V},  I_D = -2 \text{ A}$		0.052	0.07	Ω
	On–Resistance	T <sub>J</sub> =125°C		0.075	0.12	
		$V_{GS} = -2.5 \text{ V}, \qquad I_D = -1.7 \text{A},$		0.078	0.11	
		$V_{GS} = -1.8 \text{ V}, \qquad I_D = -1.2 \text{ A},$			0.21	
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, \qquad V_{DS} = -5 \text{ V}$	<b>-</b> 5			Α
<b>g</b> FS	Forward Transconductance	$V_{DS} = -4.5 \text{ V}, \qquad I_{D} = -2 \text{ A}$		8		S
Dynamic	Characteristics					
Ciss	Input Capacitance	$V_{DS} = -10 \text{ V},  V_{GS} = 0 \text{ V},$		600		pF
Coss	Output Capacitance	f = 1.0 MHz		175		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			80		pF
Switchin	ng Characteristics (Note 2)	1		ı		ı
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = -5 \text{ V}, \qquad I_D = -0.5 \text{ A},$		6	12	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V},  R_{GEN} = 6 \Omega$		9	18	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			31	50	ns
t <sub>f</sub>	Turn-Off Fall Time			26	42	ns
Qg	Total Gate Charge	$V_{DS} = -10V$ , $I_{D} = -2 A$ ,		8	11	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = -4.5 V		1.3		nC
Q <sub>gd</sub>	Gate-Drain Charge			2.2		nC
Drain-Se	ource Diode Characteristics	and Maximum Ratings		•		
ls	Maximum Continuous Drain–Source				-0.42	Α
V <sub>SD</sub>	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V},  I_S = -0.42 \text{ A}  \text{(Note)}$		-0.7	-1.2	V

#### Notes:

1.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a. 250°C/W when mounted on a 0.02in² pad of 2 oz copper

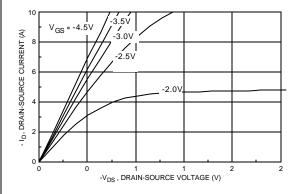


b. 270°C/W when mounted on a .001 in² pad of 2 oz copper

Scale 1 : 1 on letter size paper

**2.** Pulse Test: Pulse Width <  $300\mu s$ , Duty Cycle < 2.0%

# **Typical Characteristics**



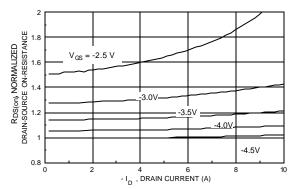
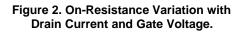
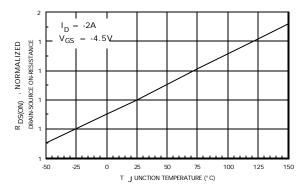


Figure 1. On-Region Characteristics.





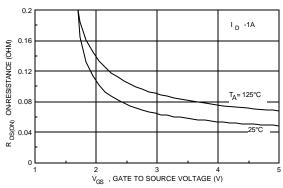
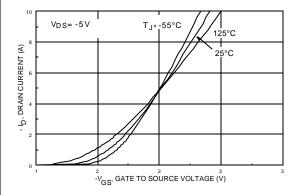


Figure 3. On-Resistance Variation withTemperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



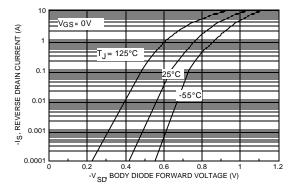
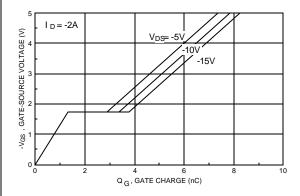


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

# **Typical Characteristics**



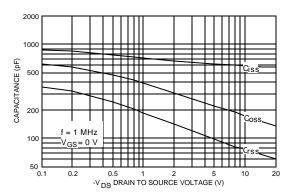


Figure 7. Gate Charge Characteristics.

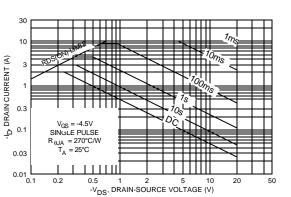


Figure 8. Capacitance Characteristics.

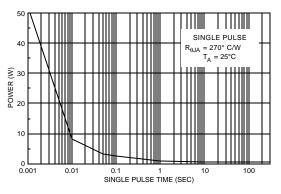


Figure 9. Maximum Safe Operating Area.



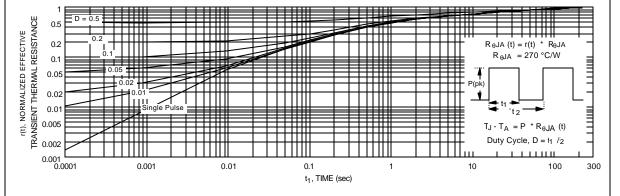
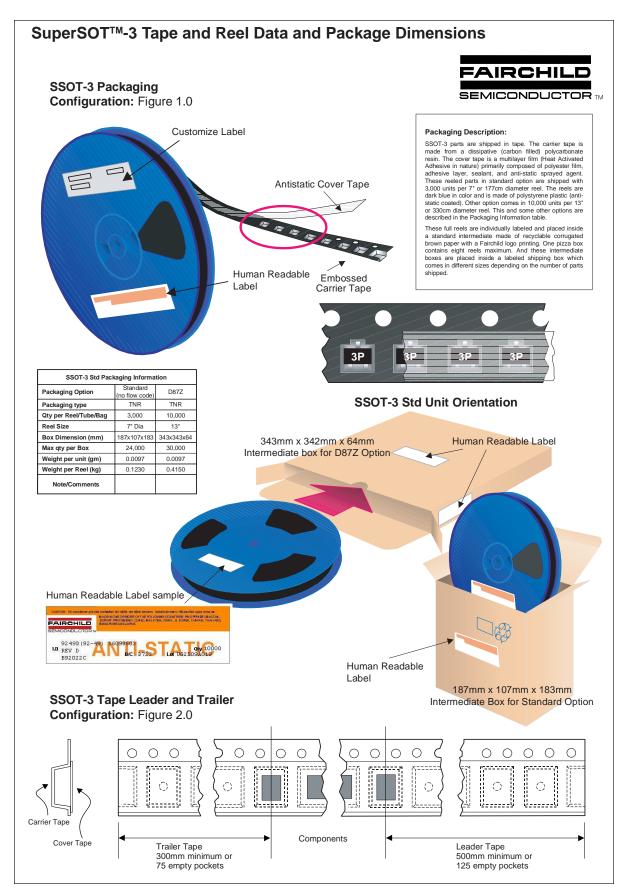


Figure 11. Transient Thermal Response Curve.

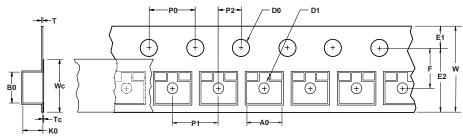
Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

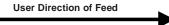




# SSOT-3 Embossed Carrier Tape

Configuration: Figure 3.0



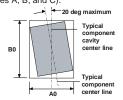


	Dimensions are in millimeter													
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-3 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-02

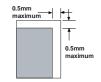
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

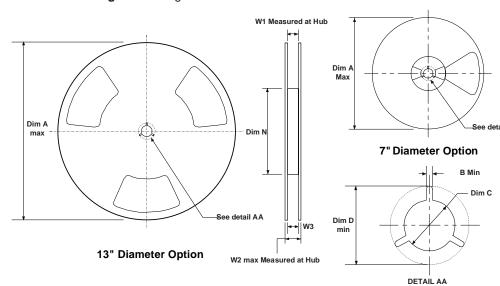


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

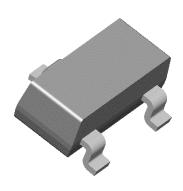
# SSOT-3 Reel Configuration: Figure 4.0

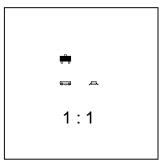


Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

# SuperSOT™-3 Tape and Reel Data and Package Dimensions, continued

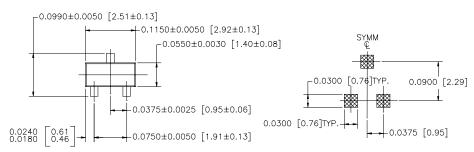
# SuperSOT™-3 (FS PKG Code 32)



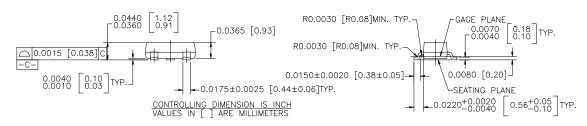


Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0097



LAND PATTERN RECOMMENDATION



NOTES: UNLESS OTHERWISE SPECIFIED

SUPER SOT , 3 LEADS

- 1. STANDARD LEAD FINISH TO BE 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN/LEAD (SOLDER) ON COPPER.
- 2. NO JEDEC REGISTRATION AS OF DEC. 1995.

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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